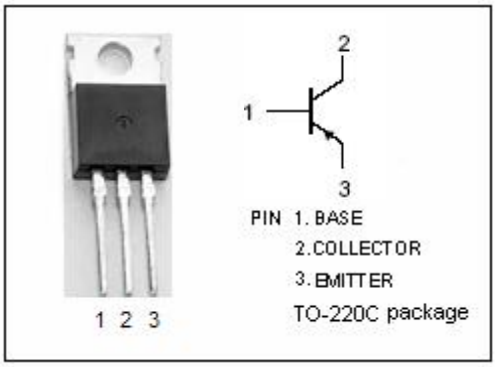
isc Silicon PNP Power Transistor 2SA1112

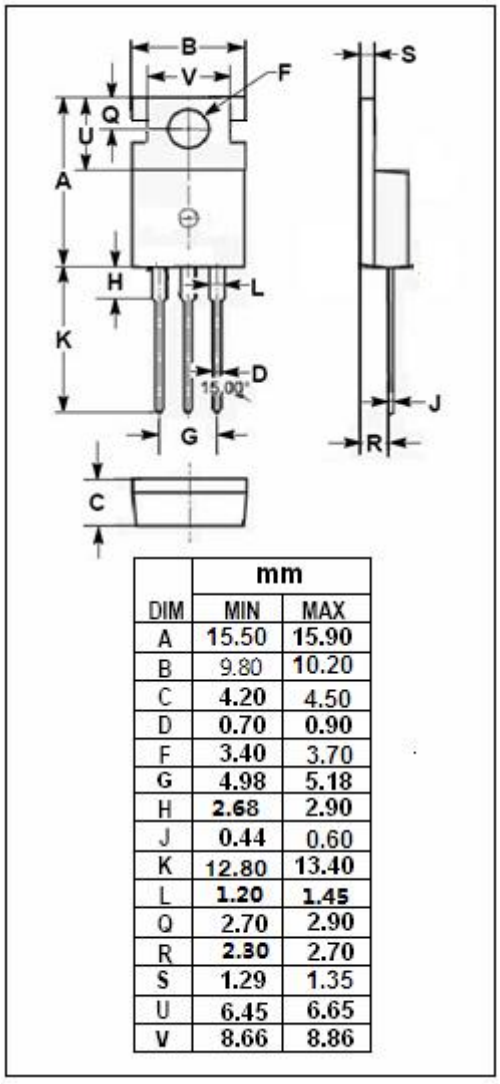


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= -180V (Min)
- Good Linearity of h_{FE}
- Complement to Type 2SC2592
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio frequency drivers and high power amplifier applications.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-180	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-1	A
I_{CM}	Collector Current-Peak	-1.5	A
P_C	Collector Power Dissipation	20	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -100 μ A; I_B= 0	-180			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -10 μ A; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-2.0	V
h_{FE-1}	DC Current Gain	I_C= -150mA; V_{CE}= -10V	65		330	
h_{FE-2}	DC Current Gain	I_C= -500mA; V_{CE}= -5V	50			
f_T	Current-Gain—Bandwidth Product	I_E= 50mA; V_{CE}= -10V		200		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1.0MHz		30		pF

◆ **h_{FE-1} Classifications**

P	Q	R	S
65-110	90-155	130-220	185-330